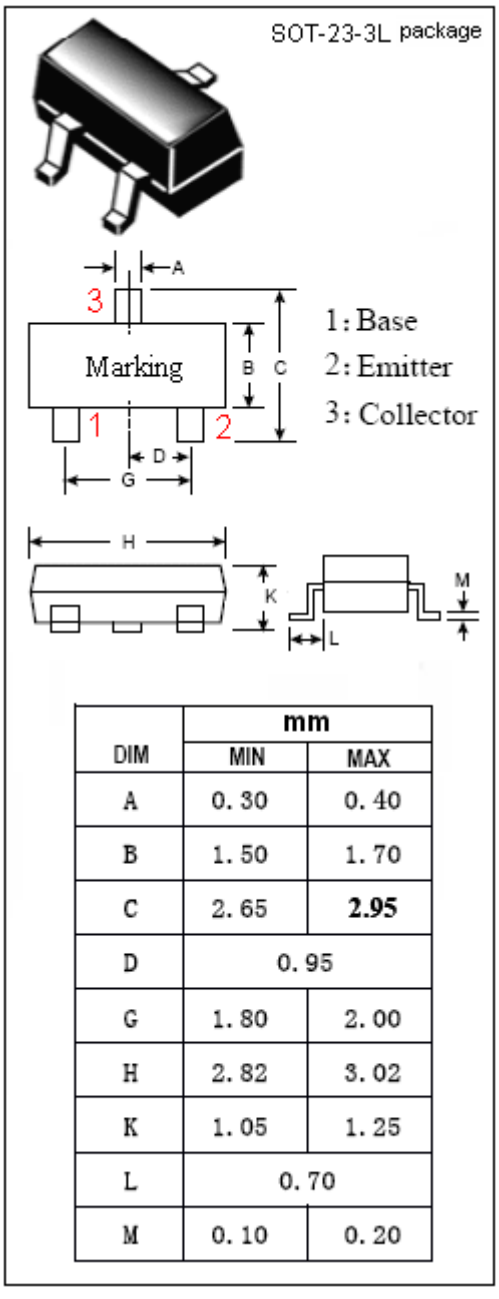
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DESCRIPTION

- High Current-Gain Bandwidth Product:
  f_T = 4 GHz TYP.
- Low Output Capacitance-
  C_{OB} = 1.5 pF TYP.
- Low Base Time Constant:
  $r_{bb'} \cdot C_C$= 4.0 ps TYP.

APPLICATIONS

- Designed for use as UHF oscillators and a UHF mixer in a tuner of a TV receiver.



DIM	mm	
	MIN	MAX
A	0.30	0.40
B	1.50	1.70
C	2.65	2.95
D	0.95	
G	1.80	2.00
H	2.82	3.02
K	1.05	1.25
L	0.70	
M	0.10	0.20

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	25	V
V_{CEO}	Collector-Emitter Voltage	12	V
V_{EBO}	Emitter-Base Voltage	3	V
I_C	Collector Current-Continuous	30	mA
P_C	Collector Power Dissipation @T_C=25℃	0.2	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

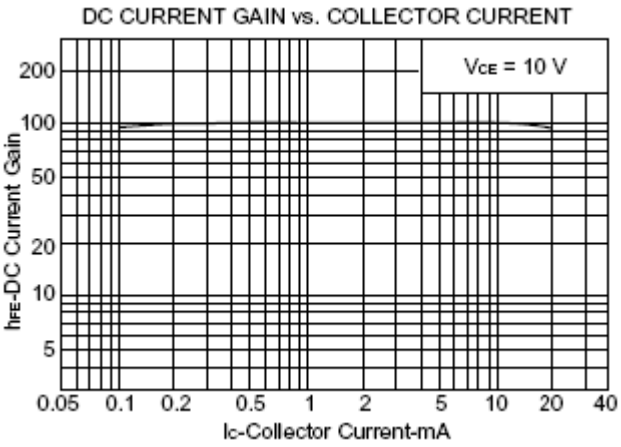
T_C=25℃ unless otherwise specified

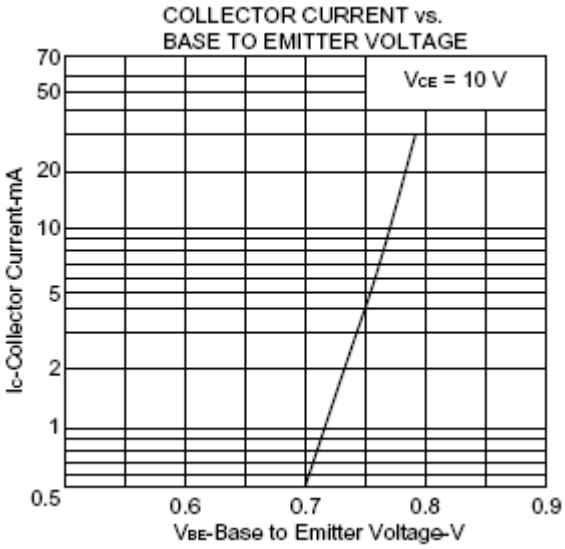
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I_{CBO}	Collector Cutoff Current	V_{CB}= 10V; I_E= 0			0.1	μA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 10mA ; I_B= 1mA			0.5	V
h_{FE}	DC Current Gain	I_C= 5mA ; V_{CE}= 10V	40		200	
f_T	Current-Gain—Bandwidth Product	I_E= -5mA;V_{CE}= 10V	2.5	4.0		GHz
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= 10V; f= 1MHz		0.85	1.5	pF
$r_{bb'} \cdot C_C$	Base Time Constant	I_E= -5mA ; V_{CE}= 10V;f= 31.9MHz		4	10	ps

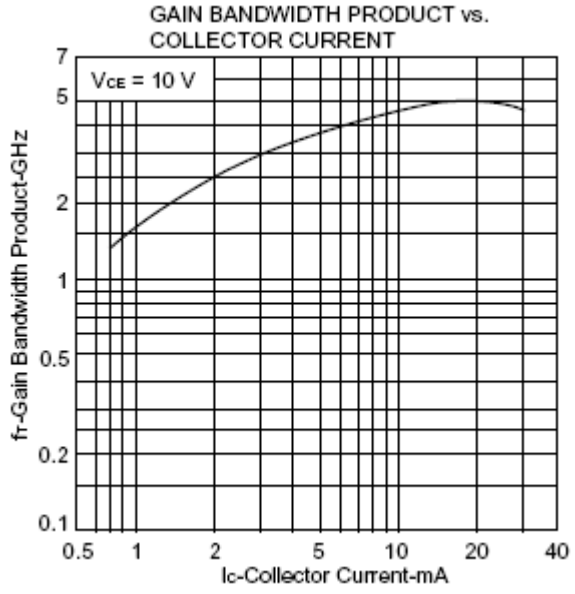
◆ **h_{FE} Classification**

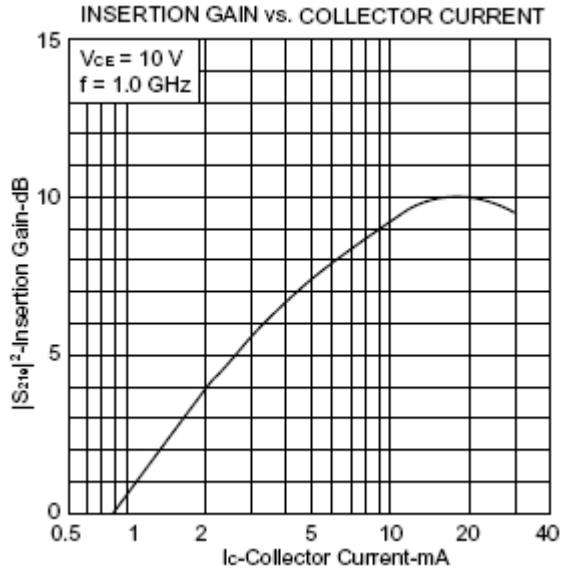
Class	T62/P	T63/Q	T64/R
Marking	T62	T63	T64
h_{FE}	40-80	60-120	100-200

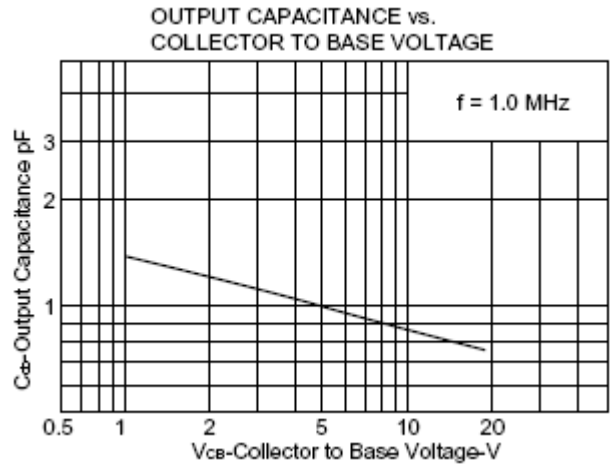
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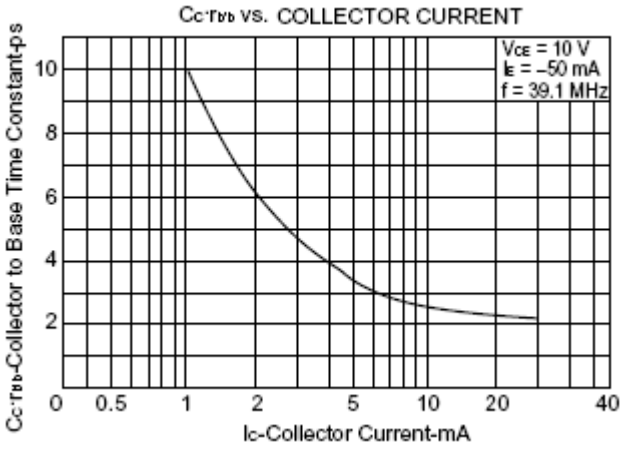












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S-PARAMETER

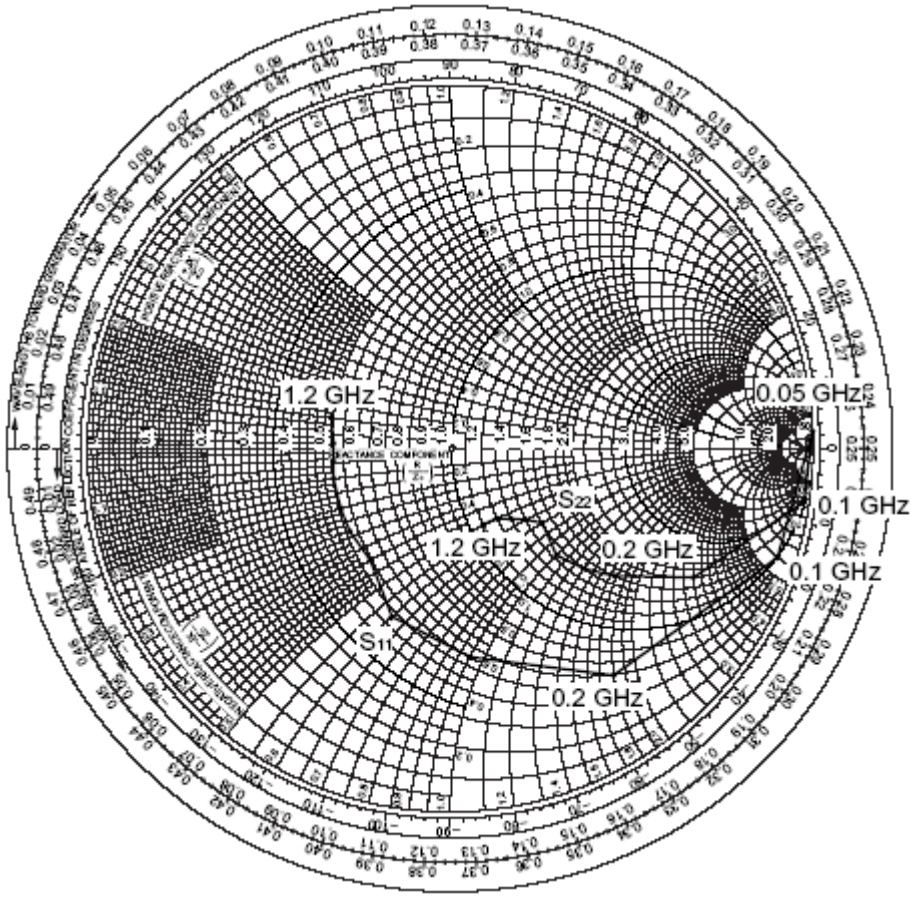
V_{CE} = 10 V, I_C = 5 mA , Z_O = 50 Ω

Freque.	S_{11}		S_{21}		S_{12}		S_{22}	
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
50	1.047	3	14.240	-178	0.003	42	1.012	3
100	0.944	-18	13.693	164	0.026	81	0.989	-10
200	0.750	-56	10.802	137	0.058	66	0.759	-30
300	0.562	-84	8.270	118	0.078	59	0.582	-39
400	0.468	-106	6.449	105	0.091	58	0.484	-40
500	0.394	-123	5.399	97	0.106	58	0.417	-45
600	0.372	-138	4.421	89	0.120	59	0.343	-44
700	0.359	-150	3.824	83	0.133	59	0.309	-48
800	0.343	-164	3.388	77	0.146	58	0.288	-53
900	0.339	-172	3.020	73	0.158	59	0.292	-54
1000	0.320	178	2.692	67	0.172	59	0.279	-61
1100	0.339	170	2.483	64	0.188	59	0.279	-57
1200	0.351	168	2.291	61	0.204	59	0.279	-61

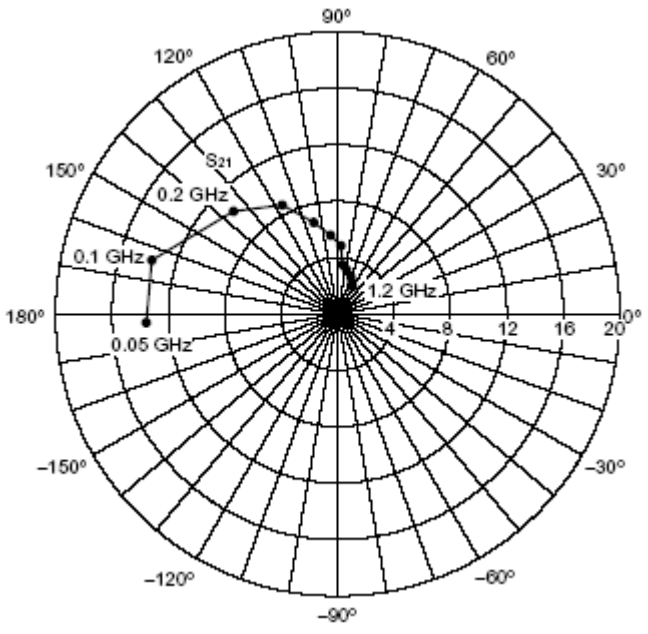
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S-PARAMETER

S_{11e}, S_{22e}-FREQUENCY CONDITION V_{CE} = 10 V, I_C = 5 mA, Z_O = 50 Ω



S_{21e}-FREQUENCY CONDITION V_{CE} = 10 V, I_C = 5 mA



S_{12e}-FREQUENCY CONDITION V_{CE} = 10 V, I_C = 5 mA

